

Amendments to the Specification:

Please add the following new paragraph after the heading **Detailed Description of the Invention:**

[0014.1] As a preliminary manner, it is noted that, in the following description, like reference numbers appearing in different drawing figures refer to like elements/features. Often, therefore, like elements/features that appear in different drawing figures will not be described in detail with respect to each of the drawing figures.

Please replace paragraph [0015] with the following amended paragraph:

[0015] FIG. 1 illustrates a plurality of quasi-coax transmission lines 100, 102 formed in accordance with the teachings of Casey, et al.'s patent application entitled "Methods for Making Microwave Circuits", cross-referenced supra. As defined herein, a quasi-coax transmission line 100 comprises a conductor 104, the cross-section of which is shielded ~~406, 408~~(e.g., by shields 106, 108) in a non-symmetrical fashion.

Please replace paragraph [0022] with the following amended paragraph:

[0022] FIG. 4 illustrates a first method 400 for forming the shielded transmission lines 200, 202, 204 shown in FIGS. 2 & 3. To begin, first and second lower mounds of dielectric 500, 502 are deposited [[402]](at step 402) on a first ground shield 218, as shown in FIG. 5. Conductors 210, 212 are then deposited [[404]](at step 404) on each of the first and second lower mounds 500, 502, and first and second upper mounds of dielectric 504, 506 are deposited [[406]](at step 406) on the first and second lower mounds of dielectric 500, 502. Thereafter, a second ground shield 220 is deposited [[408]](at step 408) over the first and second dielectrics 500, 502, 504,

506. Referring to FIG. 6, a third lower dielectric 600 is deposited [[410]](at step 410) in a valley between the first and second dielectrics 500, 502, 504, 506, and a conductor 216 is deposited [[412]](at step 412) thereon. A third upper dielectric 602 is then deposited [[414]](at step 414) on the third lower dielectric 600, and a third ground shield 222 is deposited [[416]](at step 416) over the third upper dielectric 602.

Please replace paragraph [0024] with the following amended paragraph:

[0024] FIG. 7 illustrates a second method 700 for forming the shielded transmission lines 200, 202, 204 shown in FIGS. 2 & 3. To begin, first and second lower mounds of dielectric 800, 802 are deposited [[702]](at step 702) on a first ground shield 218, as shown in FIG. 8. Ground shield walls 804, 806, 810, 812 are then deposited [[704]](at step 704) on sides of the first and second lower mounds 800, 802. Thereafter, a third lower dielectric 808 is deposited [[706]](at step 706) in a valley between the first and second lower mounds of dielectric 800, 802, and conductors 210, 212, 216 are deposited [[708]](at step 708) on each of the lower dielectrics 800, 802, 808. Referring to FIG. 9, following deposition of the conductors 210, 212, 216, first and second upper mounds of dielectric 900, 902 are deposited [[710]](at step 710) on the first and second lower mounds of dielectric 800, 802. Ground shield caps 904, 906 are then deposited [[712]](at step 712) over the first and second upper mounds of dielectric 900, 902. Thereafter, a third upper dielectric 908 is deposited [[714]](at step 714) on the third lower dielectric 808, and a second ground shield 222 is deposited [[716]](at step 716) over the third upper dielectric 908.